

Title (en)

METHOD FOR PRODUCING A FERROELECTRIC LAYER

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER FERROELEKTRISCHEN SCHICHT

Title (fr)

PROCEDE DE PRODUCTION D'UNE COUCHE FERRO-ELECTRIQUE

Publication

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Application

**EP 01911688 A 20010222**

Priority

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Abstract (en)

[origin: WO0163658A1] The invention relates to a method for producing a ferroelectric layer. According to the invention, the application of an outer electrical field facilitates the crystallisation of the material in accordance with a predetermined direction. In this way, it is possible to produce ferroelectric layers whose domains are preferably aligned in such a way that their polarisation vectors are positioned perpendicularly to the electrodes of the storage capacitor in a storage cell. As a result, the overall polarisation vector for the domains runs essentially parallel to the field of the storage capacitor while the storage device is in operation and the polarisation produced has a correspondingly high level of remanence. The level of the signal that can be read out of the storage capacitors is also correspondingly high.

IPC 1-7

**H01L 21/316**

IPC 8 full level

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